





60V NPN MEDIUM POWER TRANSISTOR IN SOT89

Features

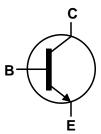
- BV_{CEO} > 60V
- Ic = 1A Continuous Collector Current
- I_{CM} = 2A Peak Pulse Current
- $R_{CE(sat)} = 195m\Omega$ for a Low Equivalent On-Resistance
- hFE Characterized up to 2A for High Current Gain Hold-Up
- Complementary PNP Type: FCX591
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

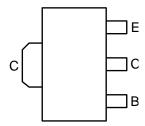
- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.055 grams (Approximate)



Top View



Equivalent Circuit



Top View Pin-Out

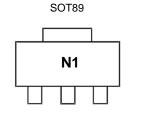
Ordering Information (Notes 4 and 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FCX491TA	AEC-Q101	N1	7	12mm	1,000
FCX491QTA	Automotive	N1	7	12mm	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N1= Product Type Marking Code





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Current	I _{CM}	2	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 6)		1	
Power Dissipation	(Note 7)	P_{D}	1.5	W
	(Note 8)		2.0	
	(Note 6)		125	
Thermal Resistance, Junction to Ambient Air	(Note 7)	R _{0JA}	83	
	(Note 8)		60	°C/W
Thermal Resistance, Junction to Lead	(Note 9)	$R_{ heta JL}$	22	
Thermal Resistance, Junction to Case	(Note 10)	R ₀ JC	16	
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C	

ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

 8. Same as Note 5, except the device is mounted on 50mm x 50mm 1oz copper.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pad).

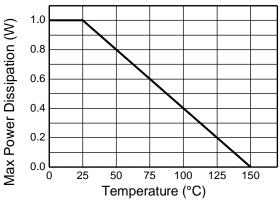
 10. Thermal resistance from junction to the top of the case.

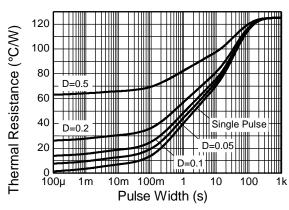
 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





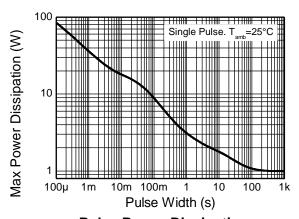
Thermal Characteristics and Derating Information



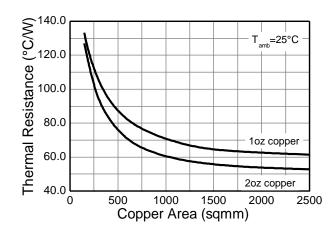


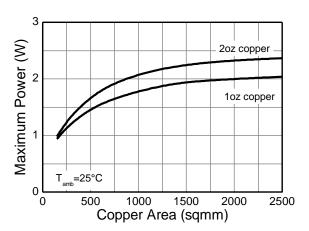
Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation









Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

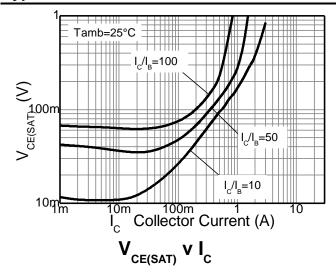
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	80	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 12)	BV_CEO	60	_	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.1	_	V	$I_E = 100\mu A$
Collector-Base Cut-Off Current	I _{CBO}	_	<1	100	nA	$V_{CB} = 60V$
Collector Cut-Off Current	I _{CES}	_	<1	100	nA	V _{CES} = 60V
Emitter Cut-Off Current	I _{EBO}	_	<1	100	nA	$V_{EB} = 5.6V$
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	_	100 160	250 500	mV	$I_C = 500$ mA, $I_B = 50$ mA $I_C = 1$ A, $I_B = 100$ mA
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	_	965	1100	mV	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(on)}	_	830	1000	mV	$I_C = 1A, V_{CE} = 5V$
DC Current Gain (Note 12)	h _{FE}	100 100 80 30	140 150 120 40	300	_	$I_{C} = 1$ mA, $V_{CE} = 5$ V $I_{C} = 500$ mA, $V_{CE} = 5$ V $I_{C} = 1$ A, $V_{CE} = 5$ 0V $I_{C} = 2$ A, $V_{CE} = 5$ V
Transitional Frequency	f⊤	150	_	_	MHz	I _C = 50mA, V _{CE} = 10V f=100MHz
Output Capacitance	C _{obo}	_	_	10	pF	V _{CB} = 10V, f=1MHz
Turn-On Time	t _{on}	_	49	_	ns	
Delay Time	t _d	_	18	_	ns]
Rise Time	t _r	_	31	_	ns	$V_{CC} = 10V$
Turn-Off Time	t _{off}	_	476	_	ns	$I_{CC} = 0.5A$ $I_{B1} = -I_{B2} = 25mA$
Storage Time	ts		414		ns	101 - 182 - 23HIV
Fall Time	t _f		62		ns	

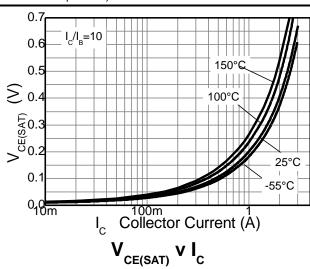
Note:

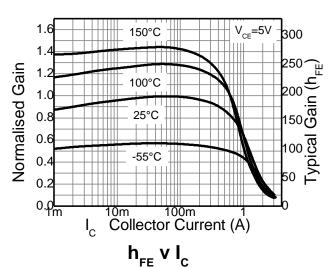
12. Measured under pulsed conditions. Pulse width \leqslant 300µs. Duty cycle \leqslant 2%

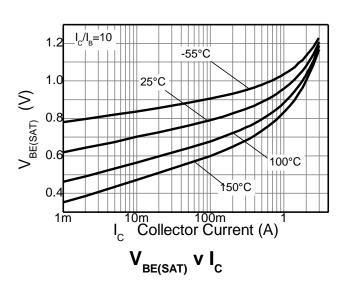


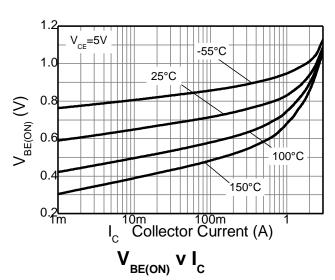
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



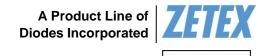






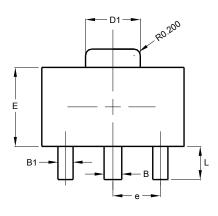


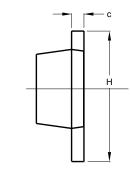


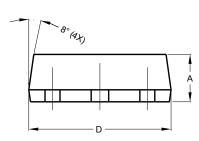


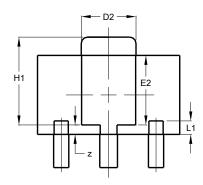
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





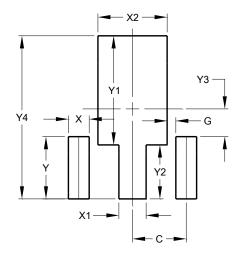




	SOT89						
Dim	Min	Max	Тур				
Α	1.40	1.60	1.50				
В	0.50	0.62	0.56				
B1	0.42	0.54	0.48				
С	0.35	0.43	0.38				
D	4.40	4.60	4.50				
D1	1.62	1.83	1.733				
D2	1.61	1.81	1.71				
Е	2.40	2.60	2.50				
E2	2.05	2.35	2.20				
е	1	-	1.50				
Н	3.95	4.25	4.10				
H1	2.63	2.93	2.78				
L	0.90	1.20	1.05				
L1	0.327	0.527	0.427				
Z	0.20	0.40	0.30				
All	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Υ	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		





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